

SiBar thyristor surge protection devices help protect sensitive telecommunication equipment from the hazards caused by lightning, power contact, and power induction. These devices have a high electrical surge capability to help protect against transient faults and a high off-state impedance, rendering them virtually transparent during normal system operation.

SiBar thyristor surge protectors assist designers to meet telecommunication and computer telephony equipment requirements and industry specifications.

Benefits:

- Helps provide protection for sensitive telecom electronic equipment
- · Low leakage current
- · Low power dissipation
- · Fast, reliable operation
- · No wear-out mechanisms
- Assists designers to meet worldwide telecom standards
- · Helps reduce warranty and service costs
- · Easy installation
- · Helps improve power efficiency of equipment

Features:

- · RoHS compliant
- · Bidirectional crowbar transient voltage protection
- Voltage range: 170V 270V
- · High off-state impedance
- · Low on-state voltage
- · High surge capability
- · Short-circuit failure mode
- · Surface-mount technology
- DO-214AC SMA package
- 10 x 1000 µs 50A surge rating
- Helps equipment comply with TIA-968, Telcordia GR-1089, IEC61000-4-5, ITU K.20/21/45

Applications:

- · Modems
- · Fax machines
- Set top boxesPOS systems
- Phones, answering machines
- PBX systems
- Analog and digital linecards (xDSL, T1/E1...)
- · Other customer premise and central office network equipment requiring protection

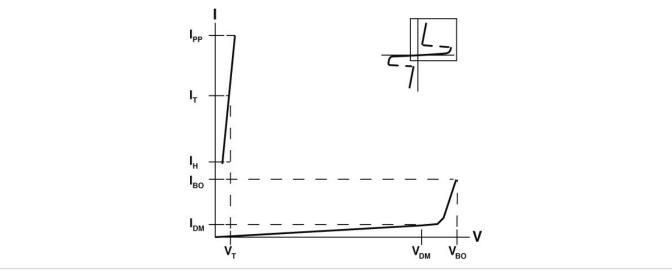


Part Number	V _{DM} Max. (V)	V _{BO} Max. (V)	I _H Min. (mA)	V _T Max. (V)	C1 (Typ) 50V _{DC} Bias	C2 (Typ) 2V _{DC} Bias	Off-State Current VD2=VDM (μΑ)
TVA170SA-L	170	265	150	4	20	39	5
TVA200SA-L	200	320	150	4	17	33	5
TVA270SA-L	270	365	150	4	16	31	5

TIA-968		Telcordia GR-1089*		IEC61000-4-5	ITU K.20/21/45*					
	Туре А	Туре В						-		
Part Number	I _{pp} (A) 5 x 320 μs	I _{ρρ} (A) 10 x 560 μs	_{pp} (A) 10 x 160 µs	I _{ρρ} (A) 10 x 1000 με	I _{pp} (A) s 2 x 10 μs	I _{pp} (Α) 8 x 20 μs	I _{₽₽} (A) 5 x 310 µs (VOC: 10 x 700µs)	I _{⊤SM} Min. (A)	di/dt (A/µs)	dV/d1 (V/µs
TVAxxxSA-L	90	70	100	50	150	150	90	22	500	2000

di/dt: critical rate-of-rise of on-state current (pulsed power amplifier Vmax = 600V; C = 30µF). dV/dt: critical rate-of-rise of off-stage voltage (linear wave form, V_D = rated V_{B0}. Ti = 25°C

Figure SB1 - Voltage-Current Characteristics

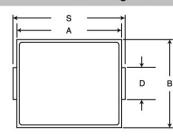


The voltage current (V-I) is useful in depicting the electrical characteristics of the SiBar thyristor surge protectors in relation to each other.

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Figure SB2 - Dimension Figure



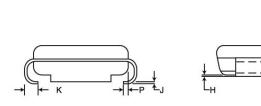


Table SB3 – Dimensions in Millimeters

		Α		в		С			D
Dimension	Min.	Max.	Mir	n. I	lax.	Min.	Max.	Min.	Max.
TVAxxxSA-L	4.06	4.57	2.2	5 2	2.92	1.90	2.41	1.25	1.65
	(0.160)	(0.180)	30.0)	39) (0	(0.115) (0.075)		(0.095)	(0.049)	(0.065)
	ŀ	1		J		к	Р	S	5
Dimension	Min.	Max.	Min.	Max.	Min.	Max.	Ref	Min	Max.
	0.051	0.200	0.150	0.41	0.76	1.52	0.051	4.80	5.59
TVAxxxSA-L		(0.008)	(0.006)	(0.016)	(0.030)	(0.060)	(0.0020)	(0.189)	(0.220)

Notes: *D dimension is measured within dimension P. TVA series devices use industry standard SMA package type. All devices are bidirectional and may be oriented in either direction for installation

Table SB4 – Physical Characteristics and Environmental Specifications

Lead material	Matte tin finish (-L devices)
Encapsulating material	Epoxy, meets UL94V-0 requirements
Solderability	per MIL-STD-750, Method 2026
Solder heat withstand	per MIL-STD-750, Method 2031
Solvent resistance	per MIL-STD-750, Method 1022
Mechanical shock	per MIL-STD-750, Method 2016
Vibration	per MIL-STD-750, Method 2056
Storage temperature (°C)	-55 to 150
Operating temperature (°C)	-40 to 125
Junction temperature (°C)	175
Maximum Lead Temperature for Soldering Purpose; for 10s (°C)	260

Table SB5 – Reliability Tests

Test	Conditions	Duration
High temperature, reverse bias	+100°C, 50VDC bias	1000 hours
High humidity, high temperature, reverse bias	85% RH, +85°C, 50VDC bias	1000 hours
High temperature storage life	+150°C	1000 hours
Temperature cycling	-65°C to +150°C, 15 minute dwell	1000 cycles
Autoclave	100% RH, +121°C, 15 PSI	96 hours



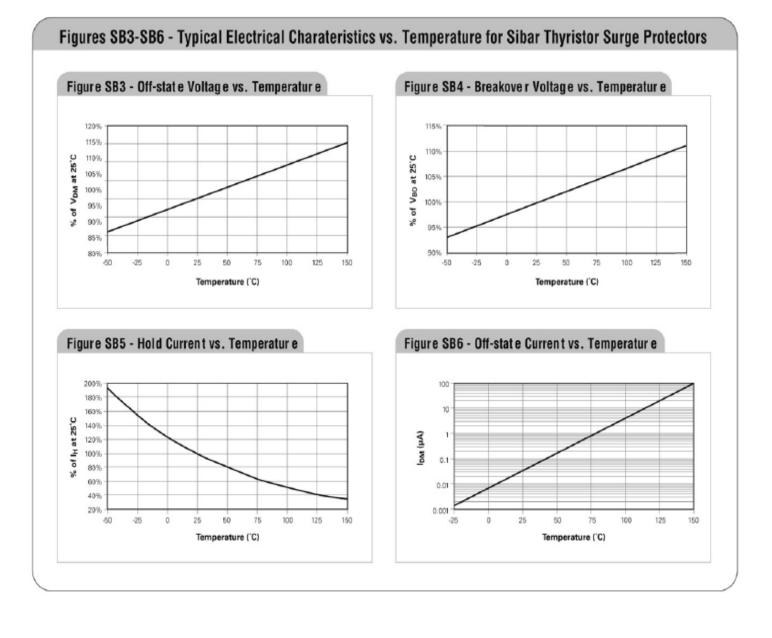




Figure SB7 - Recommended Pad Layout

Table SB6 – Packaging and Marking Information

Part Description	Tape and Reel Quantity	Standard Package	Part Marking	Dimension A (Nom.)	Dimension B (Nom.)	Dimension C (Nom.)	Agency Recognition*
TVA170SA-L	5,000	20,000	170S	2.0 (0.079)	2.0 (0.079)	2.0 (0.079)	UL
TVA220SA-L	5,000	20,000	200A	2.0 (0.079)	2.0 (0.079)	2.0 (0.079)	UL
TVA275SA-L	5,000	20,000	270A	2.0 (0.079)	2.0 (0.079)	2.0 (0.079)	UL



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